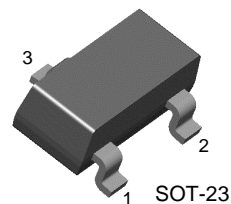


# KST5550

KST5550

## High Voltage Transistor



1. Base 2. Emitter 3. Collector

## NPN Epitaxial Silicon Transistor

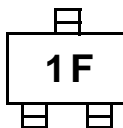
### Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

| Symbol    | Parameter                   | Value | Units            |
|-----------|-----------------------------|-------|------------------|
| $V_{CBO}$ | Collector-Base Voltage      | 160   | V                |
| $V_{CEO}$ | Collector-Emitter Voltage   | 140   | V                |
| $V_{EBO}$ | Emitter-Base Voltage        | 6     | V                |
| $I_C$     | Collector Current           | 600   | mA               |
| $P_C$     | Collector Power Dissipation | 350   | mW               |
| $T_{STG}$ | Storage Temperature         | 150   | $^\circ\text{C}$ |

### Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

| Symbol               | Parameter                            | Test Condition   | Min.           | Max.         | Units |
|----------------------|--------------------------------------|--|----------------|--------------|-------|
| $BV_{CBO}$           | Collector-Base Breakdown Voltage     | $I_C=10\mu\text{A}, I_E=0$   | 160            |              | V     |
| $BV_{CEO}$           | Collector-Emitter Breakdown Voltage  | $I_C=1\text{mA}, I_B=0$  | 140            |              | V     |
| $BV_{EBO}$           | Emitter-Base Breakdown Voltage       | $I_E=10\mu\text{A}, I_C=0$   | 6              |              | V     |
| $I_{CBO}$            | Collector Cut-off Current            | $V_{CB}=100\text{V}, I_E=0$  |                | 100          | nA    |
| $I_{EBO}$            | Emitter Cut-off Current              | $V_{EB}=4\text{V}, I_C=0$  |                | 50           | nA    |
| $h_{FE}$             | DC Current Gain                      | $V_{CE}=5\text{V}, I_C=1.0\text{mA}$<br>$V_{CE}=5\text{V}, I_C=10\text{mA}$<br>$V_{CE}=5\text{V}, I_C=50\text{mA}$ | 60<br>60<br>20 | 250          |       |
| $V_{CE}(\text{sat})$ | Collector-Emitter Saturation Voltage | $I_C=10\text{mA}, I_B=1\text{mA}$<br>$I_C=50\text{mA}, I_B=5\text{mA}$   |                | 0.15<br>0.25 | V     |
| $V_{BE}(\text{sat})$ | Base-Emitter Saturation Voltage      | $I_C=10\text{mA}, I_B=1\text{mA}$<br>$I_C=50\text{mA}, I_B=5\text{mA}$   |                | 1.0<br>1.2   | V     |
| $f_T$                | Current Gain Bandwidth Product       | $I_C=10\text{mA}, V_{CE}=10\text{V}$<br>$f=100\text{MHz}$  | 100            | 300          | MHz   |
| $C_{ob}$             | Output Capacitance                   | $V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$  |                | 6.0          | pF    |

Marking



# Typical Characteristics

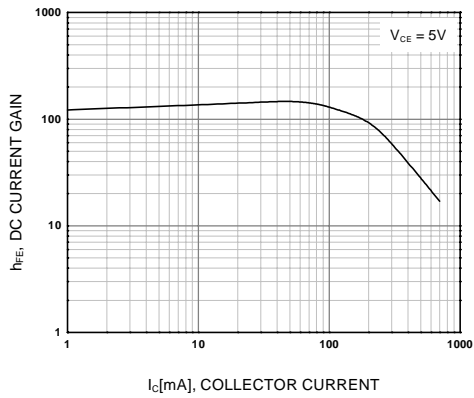


Figure 1. DC current Gain

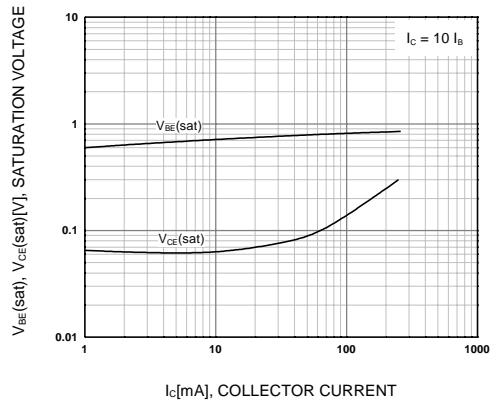


Figure 2. Base-Emitter Saturation Voltage  
Collector-Emmitter Saturation Voltage

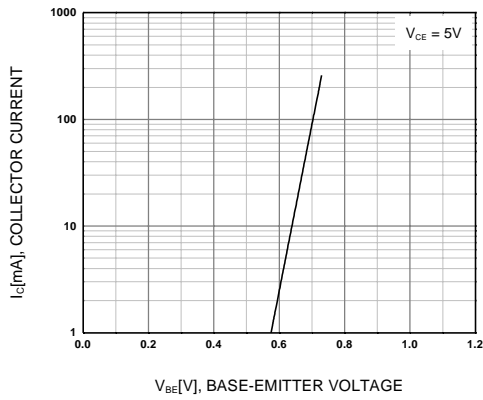


Figure 3. Base-Emitter On Voltage

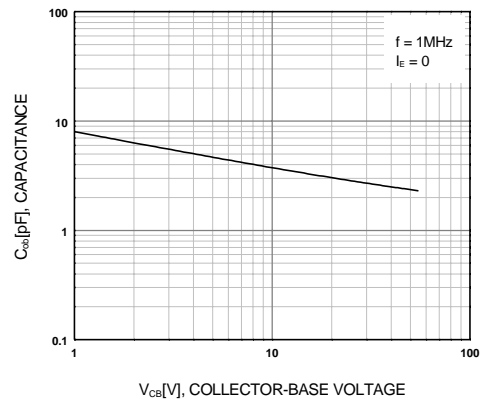


Figure 4. Output Capacitance

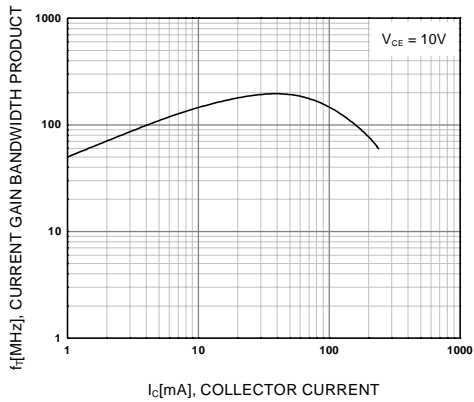


Figure 5. Current Gain Bandwidth Product

# Package Dimensions

## SOT-23



Dimensions in Millimeters

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| ActiveArray <sup>TM</sup>                         | FACT Quiet series <sup>TM</sup>  | ISOPLANAR <sup>TM</sup>         | POP <sup>TM</sup>                | Stealth <sup>TM</sup>        |
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